

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC4448

DESCRIPTION

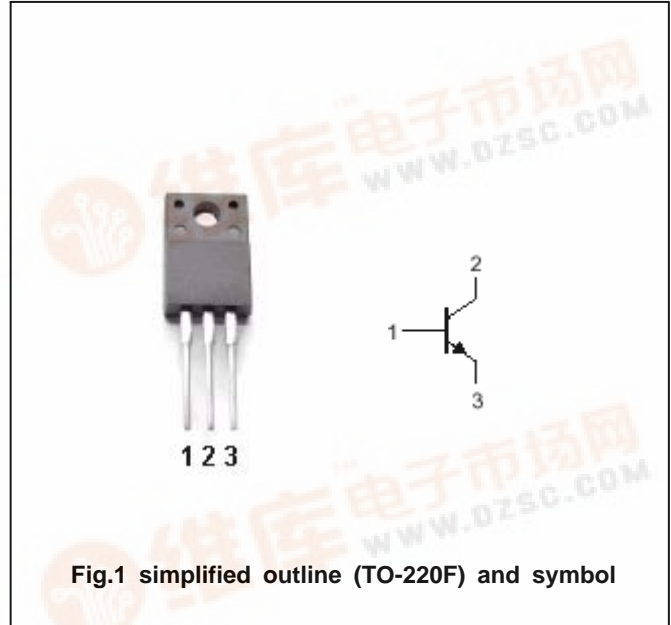
- With TO-220F package
- High voltage ,high frequency

APPLICATIONS

- Chroma output applications for HDTV
- Video output applications for high-resolution display

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	250	V
V _{CEO}	Collector-emitter voltage	Open base	250	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		150	mA
I _{CM}	Collector current-peak		300	mA
I _B	Base current		50	mA
P _C	Collector dissipation	T _a =25	2	W
		T _C =25	10	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =50mA ; I _B =5mA			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =50mA ; I _B =5mA			1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =200V; I _E =0			100	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μ A
h _{FE-1}	DC current gain	I _C =10mA ; V _{CE} =10V	40		200	
h _{FE-2}	DC current gain	I _C =100mA ; V _{CE} =10V	20			
f _T	Transition frequency	I _C =40mA ; V _{CE} =10V		240		MHz
C _{OB}	Collector output capacitance	f=1MHz; V _{CB} =30V		3.3		pF

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PACKAGE OUTLINE

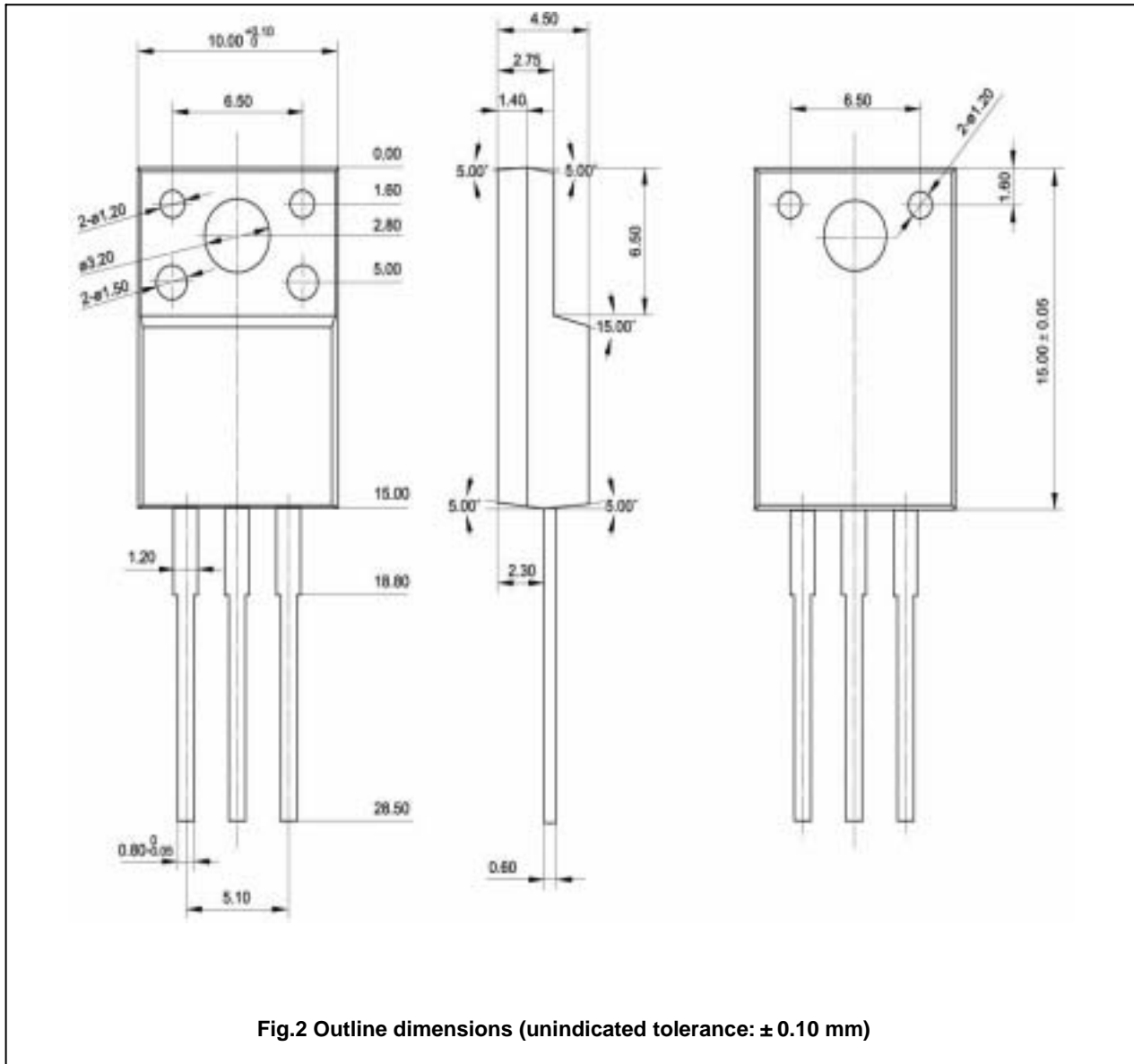


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)

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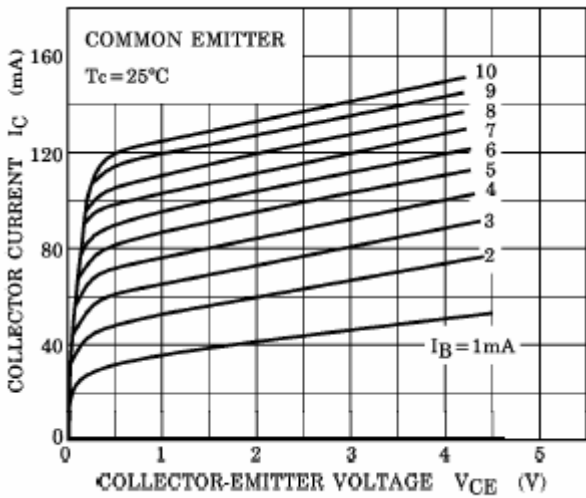


Fig.3 Static Characteristic

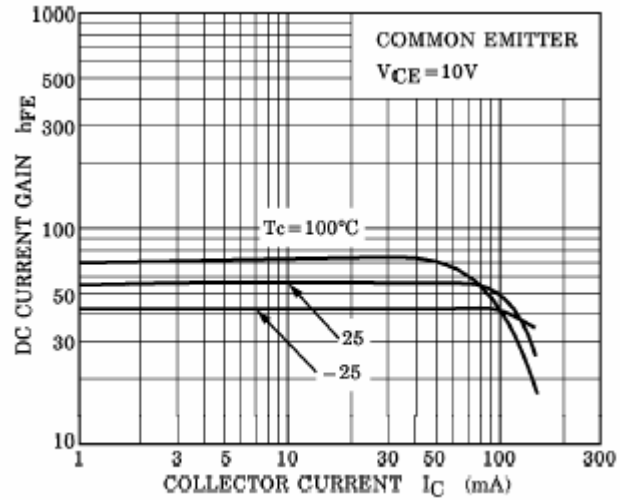


Fig.4 DC current Gain

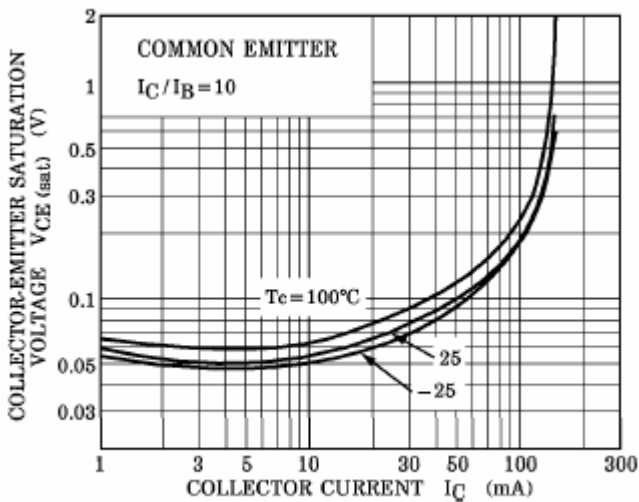


Fig.5 Collector-Emitter Saturation Voltage

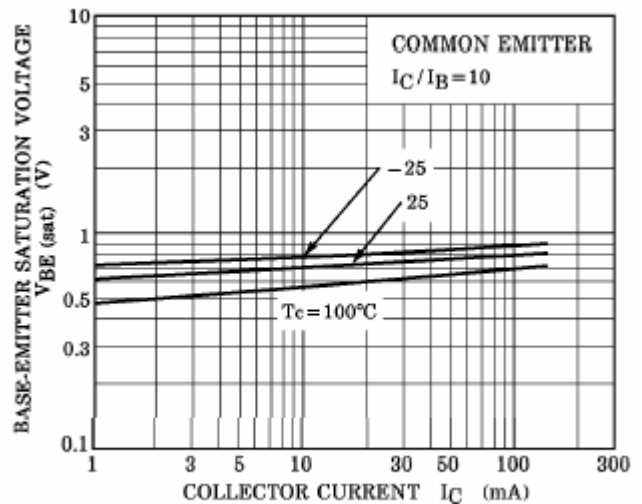


Fig.6 Base-Emitter Saturation Voltage

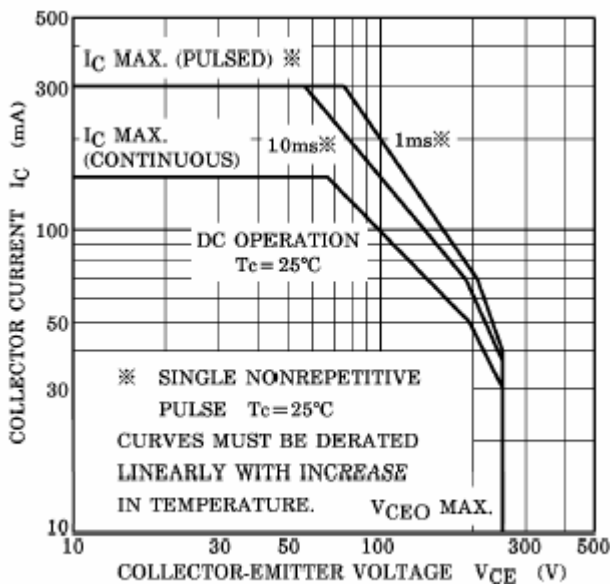


Fig.7 Safe Operating Area